

PATENT ABSTRACTS OF JAPAN

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(54) METHOD OF BAKING ALUMINUM NITRIDE SUBSTRATE

(57)Abstract:

PURPOSE: To enable mass production of AlN substrate so as to reduce the cost of a substrate by drying the specified green sheet, and then placing a tungsten wire or a molybdenum wire in the vicinity of a green sheet or printing paste capable of simultaneous baking with the green sheet so as to make a spacer, and after degreasing treatment, laminating them in a baking vessel, and baking them in nonoxidizing atmosphere.

CONSTITUTION: AlN powder is used as main constituent material, and a binder, a plasticizer, and a solvent are added to this powder and those are kneaded, and using this material a green sheet is made. Next, it is dried at room temperature, and the green sheet from which a dispersant is removed is punched out, and a spacer 6 consisting of Mo wire is placed on the AlN green sheet 5, and using a tunnel furnace, degreasing treatment is done in N₂ atmosphere. This AlN sheet is placed on a BN setter 2 in a baking vessel 4 consisting of graphite, and is baked while letting N₂ gas flow. Thereafter, it is cut along the inside of the spacer 6 by a diamond cutter so as to obtain an AlN substrate.

